

## 4.0kV 1.0A HIGH VOLTAGE DIODES

BR4 is high reliability resin molded type high voltage diode in small size package which is sealed a multilayered mesa type silicon chip by epoxy resin.

### Features

- High speed switching
- High Current
- High surge resistivity for CRT discharge
- High reliability design
- High Voltage

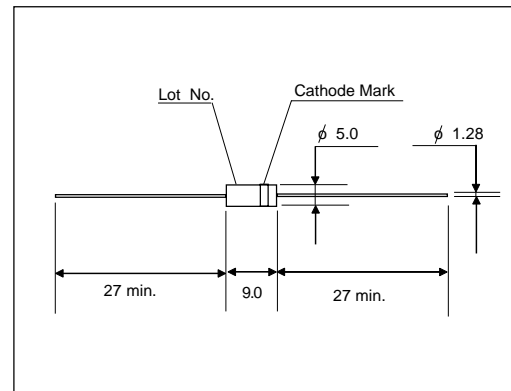
### Applications

- X light Power supply
- Laser
- Voltage doubler circuit
- Microwave emission power

### Maximum Ratings and Characteristics

- Absolute Maximum Ratings

### Outline Drawings : mm



### Cathode Mark

Type	Mark
BR4	

Items	Symbols	Condition	BR4	Units
Repetitive Peak Reverse Voltage	$V_{RRM}$		4.0	kV
Average Output Current	$I_o$	$T_a=25^{\circ}C$ , Resistive Load	1.0	A <sub>peak</sub>
Surge Current	$I_{FSM}$		20	A <sub>peak</sub>
Junction Temperature	$T_j$		155	$^{\circ}C$
Allowable Operation Case Temperature	$T_c$		125	$^{\circ}C$
Storage Temperature	$T_{stg}$		-40 to +155	$^{\circ}C$

### Electrical Characteristics ( $T_a=25^{\circ}C$ Unless otherwise specified)

Items	Symbols	Conditions	BR4	Units
Maximum Forward Voltage Drop	$V_F$	at $25^{\circ}C$ , $I_F = I_{F(AV)}$	4.4	V
Maximum Reverse Current	$I_{R1}$	at $25^{\circ}C$ , $V_R = V_{RRM}$	3.0	$\mu A$
	$I_{R2}$	at $100^{\circ}C$ , $V_R = V_{RRM}$	30	$\mu A$
Maximum Reverse Recovery Time	$T_{rr}$	at $25^{\circ}C$	--	nS
Junction Capacitance	$C_j$	at $25^{\circ}C$ , $V_R=0V$ , $f=1MHz$	--	pF